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CORRECTION

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Correction: Strain mapping inside an individual processed vertical nanowire transistor using scanning X-ray nanodiffraction

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Correction for 'Strain mapping inside an individual processed vertical nanowire transistor using scanning X-ray nanodiffraction' by Dmitry Dzhigaev *et al.*, *Nanoscale*, 2020, **12**, 14487–14493, DOI: **10.1039/D0NR02260H**.

The authors regret that the Acknowledgements section in the original manuscript was incorrect. The Acknowledgements should read as follows:

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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